Vgs	0.95	0.97	0.99	1.01	1.03	1.05	1.07	1.09	1.11	1.13	1.15
QTY	1	1	3	5	6	4	12	8	6	4	2
	2%	2%	6%	10%	12%	8%	23%	15%	12%	8%	4%

JFET DISTRIBUTION

Vgs @ 1 ohm @ Vd = 3V
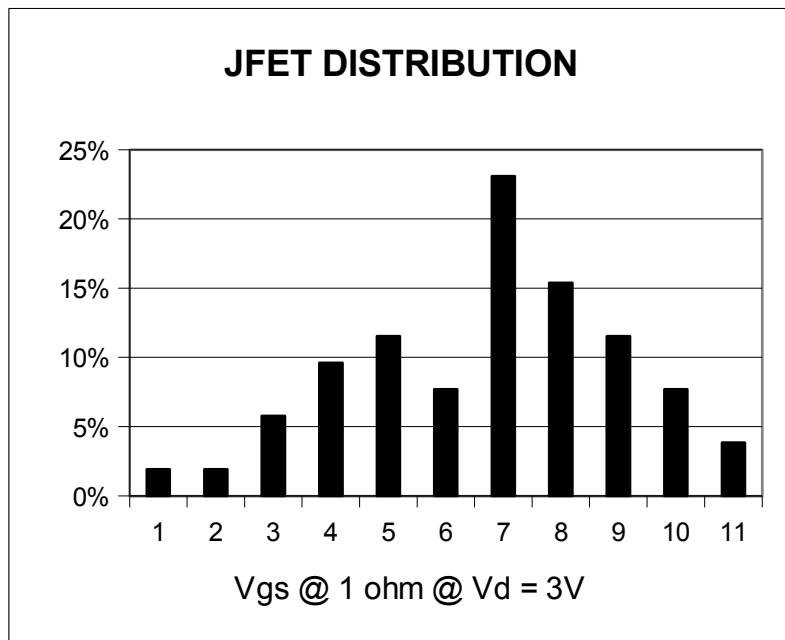
test of 3 power JFET samples with 1 ohm source resistance,
gate grounded, and supply applied to Drain of device

		supply V	2.00	2.50	3.00	3.50
sample1	Vs		0.77	0.84	0.93	0.96
	Vds		1.23	1.66	2.07	2.54
sample 2	Vs		0.90	0.98	1.07	1.11
	Vds		1.10	1.52	1.93	2.39
sample 3	Vs		0.97	1.05	1.15	1.18
	Vds		1.03	1.45	1.85	2.32

dependence on Vds of current through device (from above data)
expressed as variation of Ids vs variation of Vds

supply change	2.0-2.5V	2.5-3.0V	3.0-3.5V
sample1	0.07 A	0.09 A	0.03 A
	0.43 V	0.41 V	0.47 V
	0.16 I/V	0.22 I/V	0.06 I/V
sample 2	0.08 A	0.09 A	0.04 A
	0.42 V	0.41 V	0.46 V
	0.19 I/V	0.22 I/V	0.09 I/V
sample 3	0.08 A	0.10 A	0.03 A
	0.42 V	0.40 V	0.47 V
	0.19 I/V	0.25 I/V	0.06 I/V

Test setup for 3 sample JFETs in an F3 amplifier, adjusted for lowest distortion at 1 watt with 21 V DC output. Source resistance varied and Aleph Current Source adjusted for 13.0 dB gain

sample 1

Vgs @ 1 ohm @ Vd = 3V	0.95 v
% distortion @ 1 watt 1 KHz	0.004
Vds	2.46 v
Vs	1.03 v
Source resistance in || with 1 ohm	1.8 ohm
Source resistance	0.64
Gain pot on Aleph Current Source	740
Current Source Gain %	

sample 2

Vgs @ 1 ohm @ Vd = 3V	1.05 v
% distortion @ 1 watt 1 KHz	0.003
Vds	2.46 v
Vs	1.20 v
Source resistance in || with 1 ohm	2.9 ohm
Source resistance	0.74
Gain pot on Aleph Current Source	671
Current Source Gain %	

sample 3

Vgs @ 1 ohm @ Vd = 3V	1.15 v
% distortion @ 1 watt 1 KHz	0.003
Vds	2.46 v
Vs	1.03 v
Source resistance in || with 1 ohm	5.7 ohm
Source resistance	0.85
Gain pot on Aleph Current Source	740
Current Source Gain %	

OPTIMAL RESISTANCE IN PARALLEL WITH 1 OHM